



BUK7526-100B

N-channel TrenchMOS standard level FET

25 February 2014

Product data sheet

1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V, 24 V and 42 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_J \geq 25\text{ °C}$; $T_J \leq 175\text{ °C}$	-	-	100	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2 ; Fig. 3	-	-	49	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1	-	-	157	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_J = 25\text{ °C}$; Fig. 11 ; Fig. 12	-	22	26	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $V_{DS} = 80\text{ V}$; $T_J = 25\text{ °C}$; Fig. 13	-	13	-	nC
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 49\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\text{ Ω}$; $V_{GS} = 10\text{ V}$; $T_{J(init)} = 25\text{ °C}$; unclamped	-	-	144	mJ

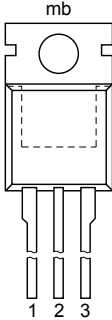
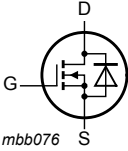


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-220AB (SOT78A)	 mbb076
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7526-100B	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7526-100B	BUK7526-100B

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$; $T_j \leq 175\text{ }^{\circ}\text{C}$	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$; Fig. 1	-	157	W
I_D	drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; $V_{GS} = 10\text{ V}$; Fig. 2; Fig. 3	-	49	A
		$T_{mb} = 100\text{ }^{\circ}\text{C}$; $V_{GS} = 10\text{ V}$; Fig. 2	-	34	A

Symbol	Parameter	Conditions		Min	Max	Unit
I_{DM}	peak drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 3		-	197	A
T_{stg}	storage temperature			-55	175	$^{\circ}\text{C}$
T_j	junction temperature			-55	175	$^{\circ}\text{C}$
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ }^{\circ}\text{C}$		-	49	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ }^{\circ}\text{C}$		-	197	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 49\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; unclamped		-	144	mJ

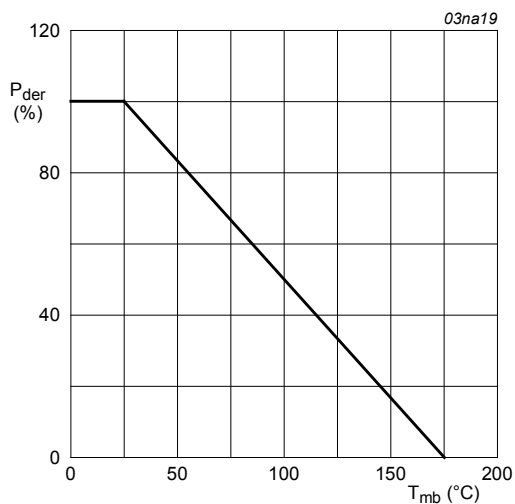


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

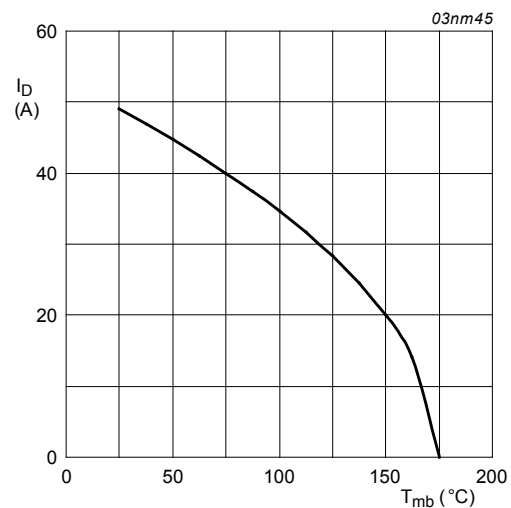


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10\text{ V}$$

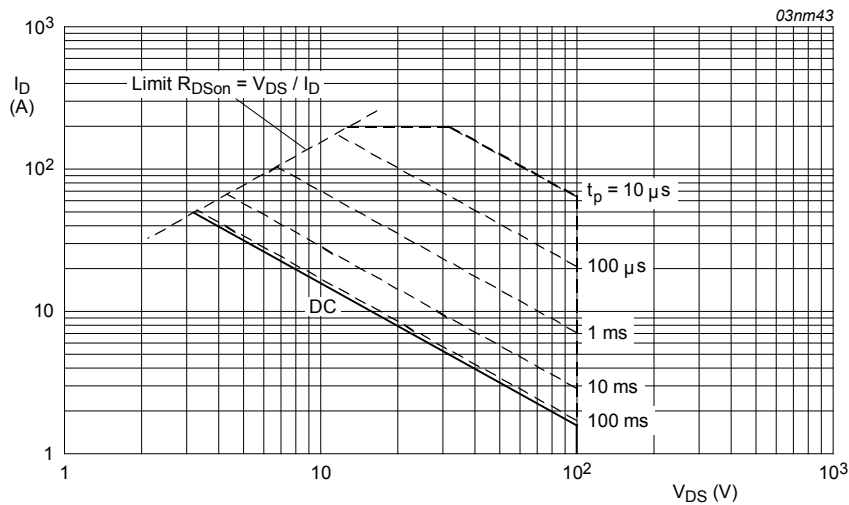


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}\text{C}; I_{DM}$ is single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	-	0.95	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	-	60	K/W

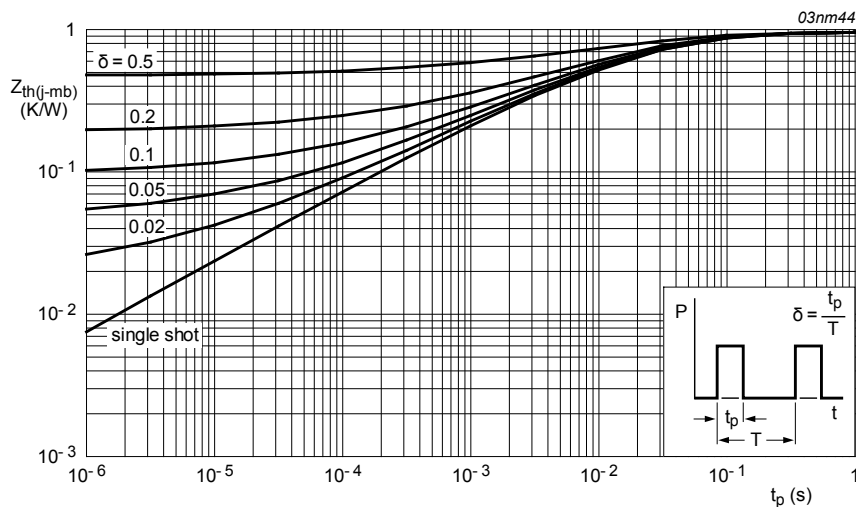


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _j = 25 °C		100	-	-	V
		I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C		89	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10		1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 10		2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 10		-	-	4.4	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C		-	-	500	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C		-	0.02	1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12		-	-	68	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11; Fig. 12		-	22	26	mΩ
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 80 V; V _{GS} = 10 V; T _j = 25 °C; Fig. 13		-	38	-	nC
Q _{GS}	gate-source charge			-	9	-	nC
Q _{GD}	gate-drain charge			-	13	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; Fig. 14		-	2168	2891	pF
C _{oss}	output capacitance			-	238	286	pF
C _{rss}	reverse transfer capacitance			-	102	140	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V; R _{G(ext)} = 10 Ω; T _j = 25 °C		-	21	-	ns
t _r	rise time			-	40	-	ns
t _{d(off)}	turn-off delay time			-	47	-	ns
t _f	fall time			-	19	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die; T _j = 25 °C		-	4.5	-	nH
		from contact screw on mounting base to centre of die; T _j = 25 °C		-	3.5	-	nH
L _S	internal source inductance	from source lead 6 mm from package to source bond pad; T _j = 25 °C		-	7.5	-	nH

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 15	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}$; $dI_S/dt = -100\text{ A}/\mu\text{s}$;	-	94	-	ns
Q_r	recovered charge	$V_{GS} = -10\text{ V}$; $V_{DS} = 30\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$	-	115	-	nC

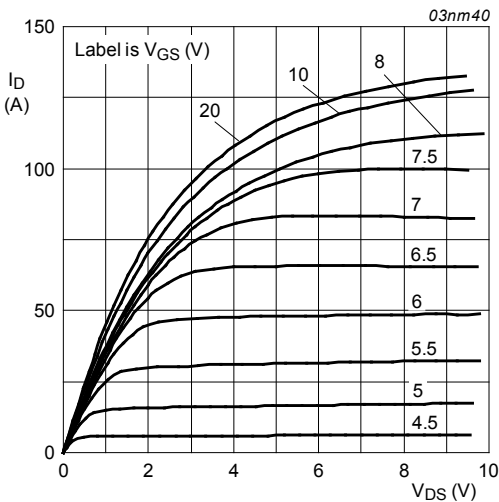


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$T_j = 25\text{ }^{\circ}\text{C}$; $t_p = 300\mu\text{s}$

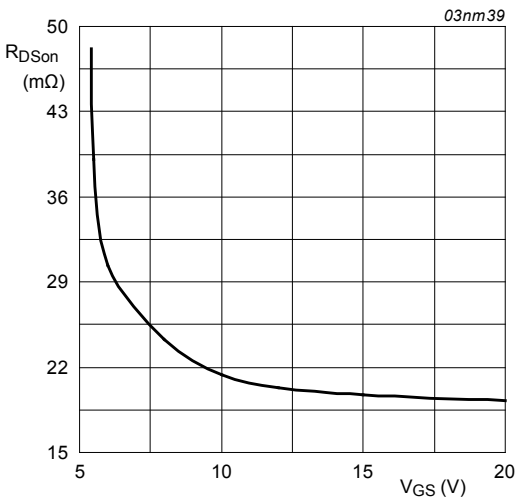


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ }^{\circ}\text{C}$; $I_D = 25\text{ A}$

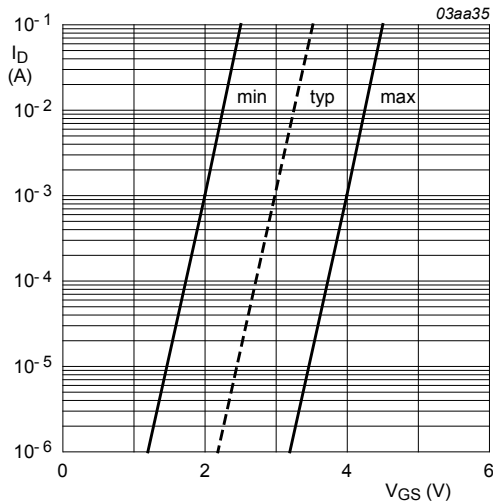


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25\text{ }^{\circ}\text{C}$; $V_{DS} = 5\text{ V}$

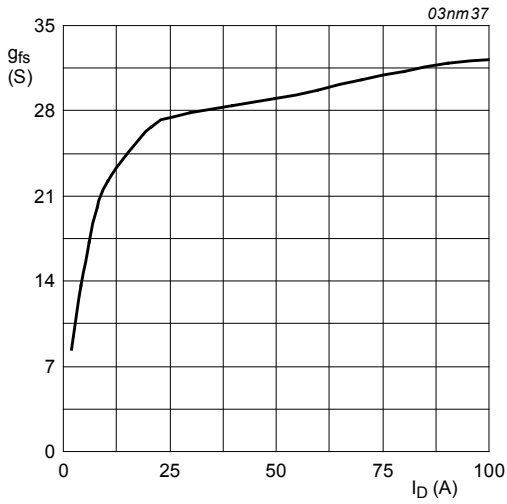


Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25\text{ }^{\circ}\text{C}$; $V_{DS} = 25\text{ V}$

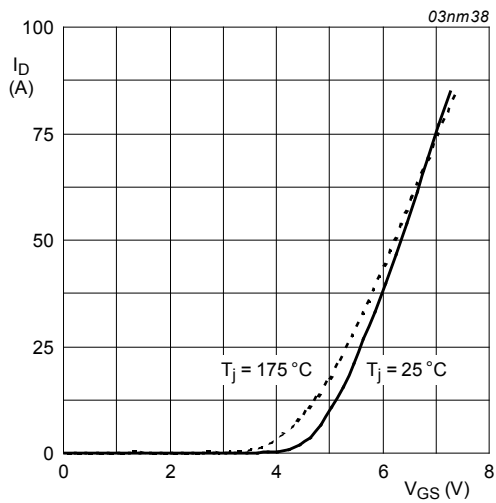


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} = 25V$$

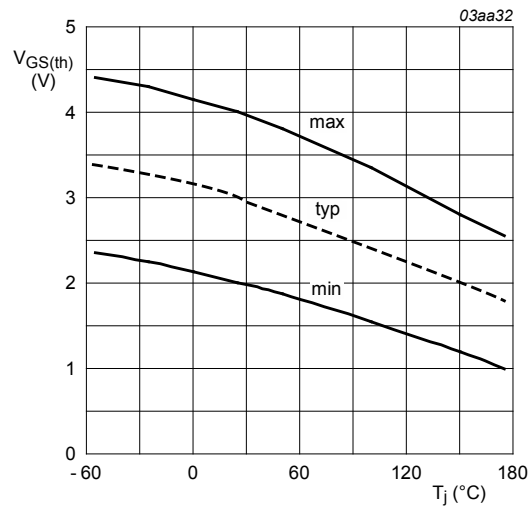


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1mA; V_{DS} = V_{GS}$$

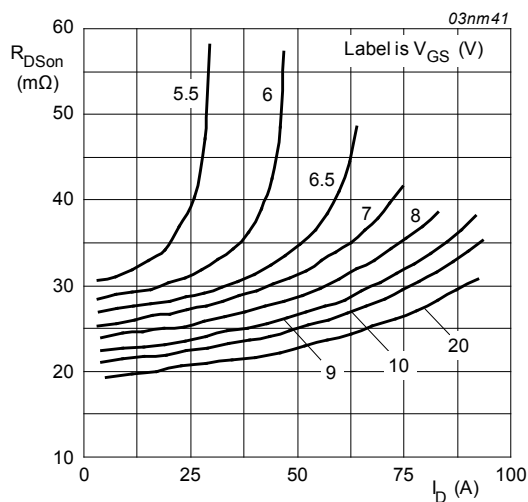


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

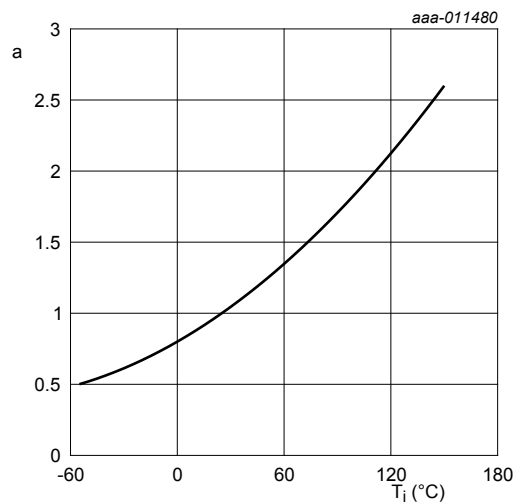


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

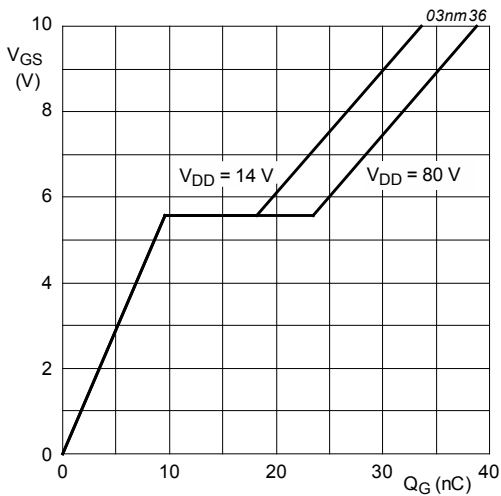


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$T_J = 25^{\circ}\text{C}; I_D = 25\text{ A}$

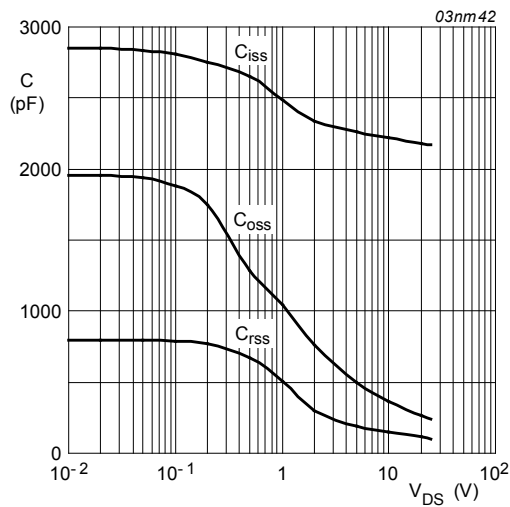


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

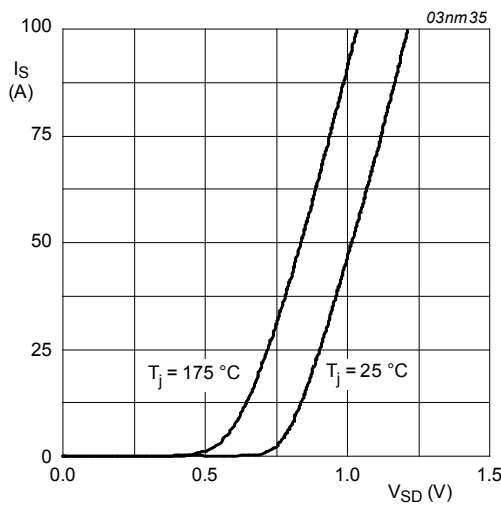


Fig. 15. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0\text{ V}$

11. Package outline

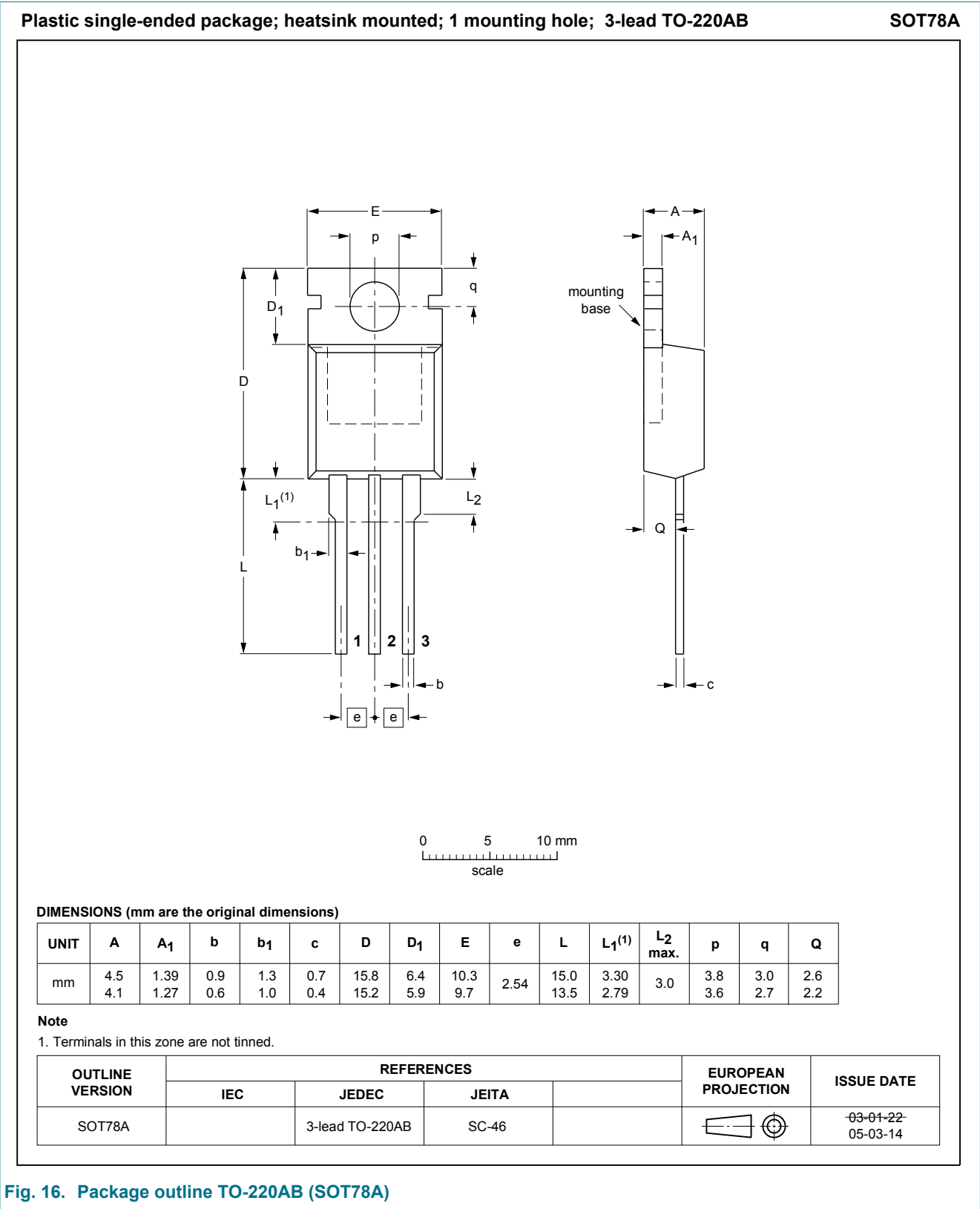


Fig. 16. Package outline TO-220AB (SOT78A)

12. Legal information

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